



412

Form 1449*

Sheet 1 of 7

INFORMATION DISCLOSURE STATEMENT
BY APPLICANT
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Atty. Docket No.: 303.378US1

Serial No. 08/903,453

Applicant: Leonard Forbes et al.

Filing Date: July 29, 1997

Group: 1104

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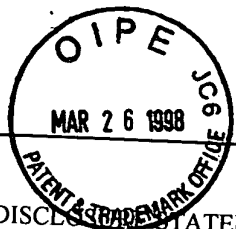
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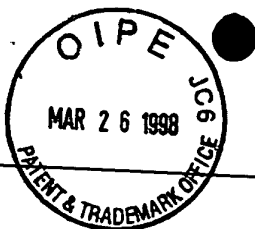
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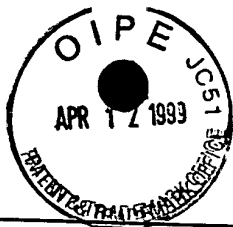
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